

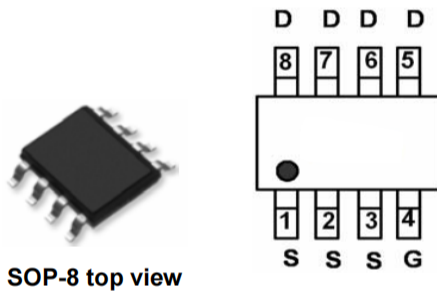
GENERAL FEATURES

- $V_{DS} = 40V$ $I_D = 15A$
- $R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=10V$

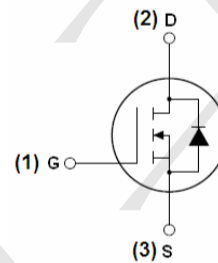
Application

- Battery protection
- Load switch

Package and Pin Configuration



Circuit diagram



Marking:15N04

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8	A
I_{DM}	Pulsed Drain Current ²	34	A
EAS	Single Pulse Avalanche Energy ³	31	mJ
I_{AS}	Avalanche Current	25	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	65	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	30	$^\circ C/W$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.034	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	---	10	13	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=4.5V, I_D=6A$	---	13	17	
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=8A$	---	36	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=8A$	---	10.7	---	nC
Q_{gs}	Gate-Source Charge		---	3.3	---	
Q_{gd}	Gate-Drain Charge		---	4.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V, V_{GS}=10V, R_G=3.3\Omega, I_D=6A$	---	8.6	---	ns
T_r	Rise Time		---	3.4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.8	---	
T_f	Fall Time		---	2.2	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	1314	---	pF
C_{oss}	Output Capacitance		---	120	---	
C_{rss}	Reverse Transfer Capacitance		---	88	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	8.5	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	34	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

Typical Characteristics

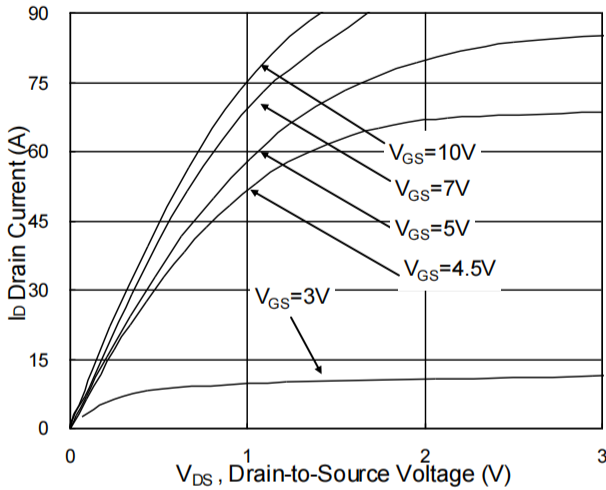


Fig.1 Typical Output Characteristics

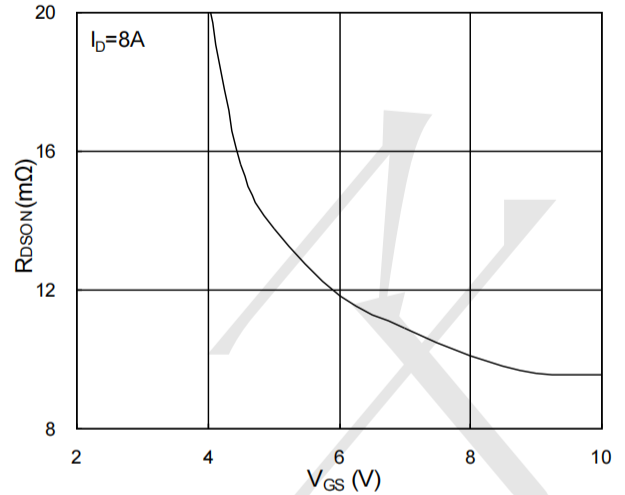


Fig.2 On-Resistance vs. G-S Voltage

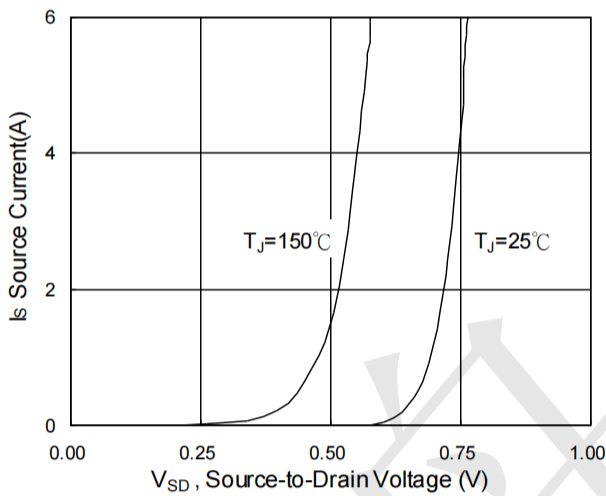


Fig.3 Forward Characteristics of Reverse

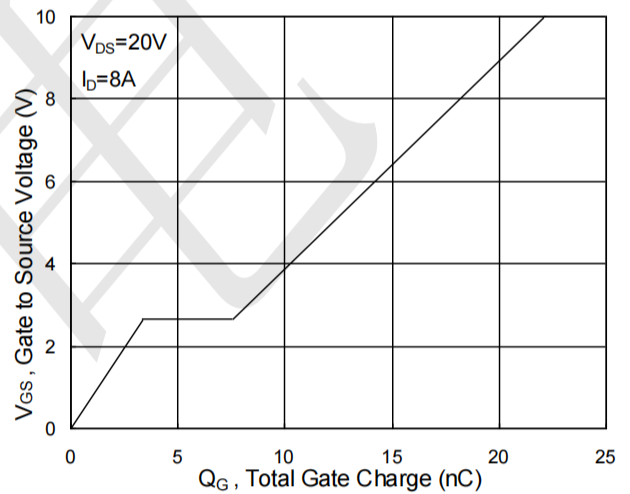


Fig.4 Gate-Charge Characteristics

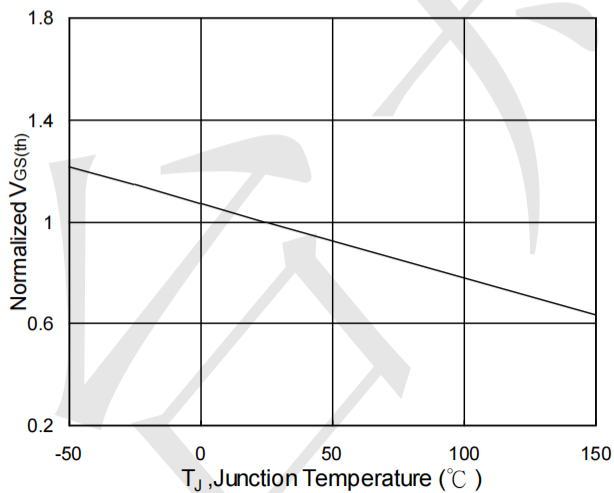


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

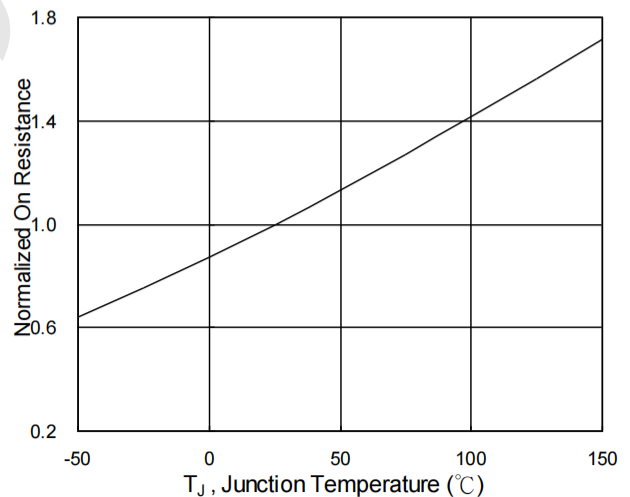


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

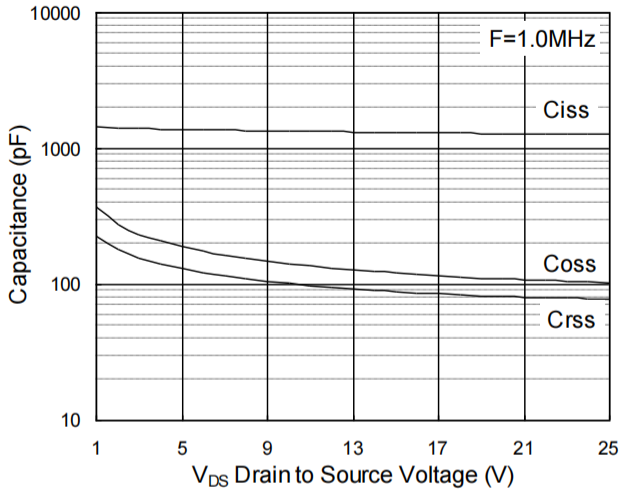


Fig.7 Capacitance

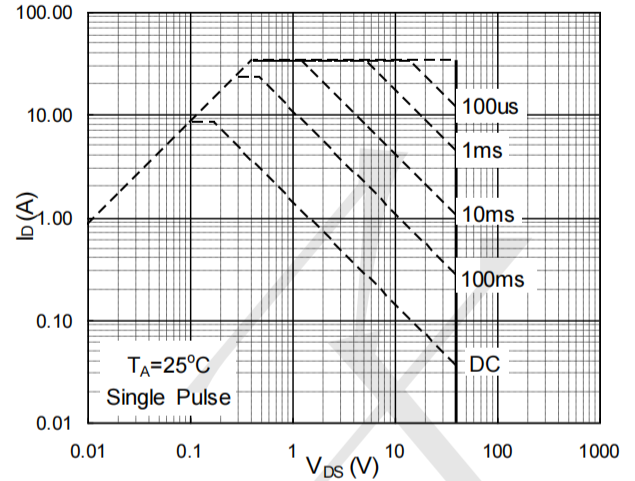


Fig.8 Safe Operating Area

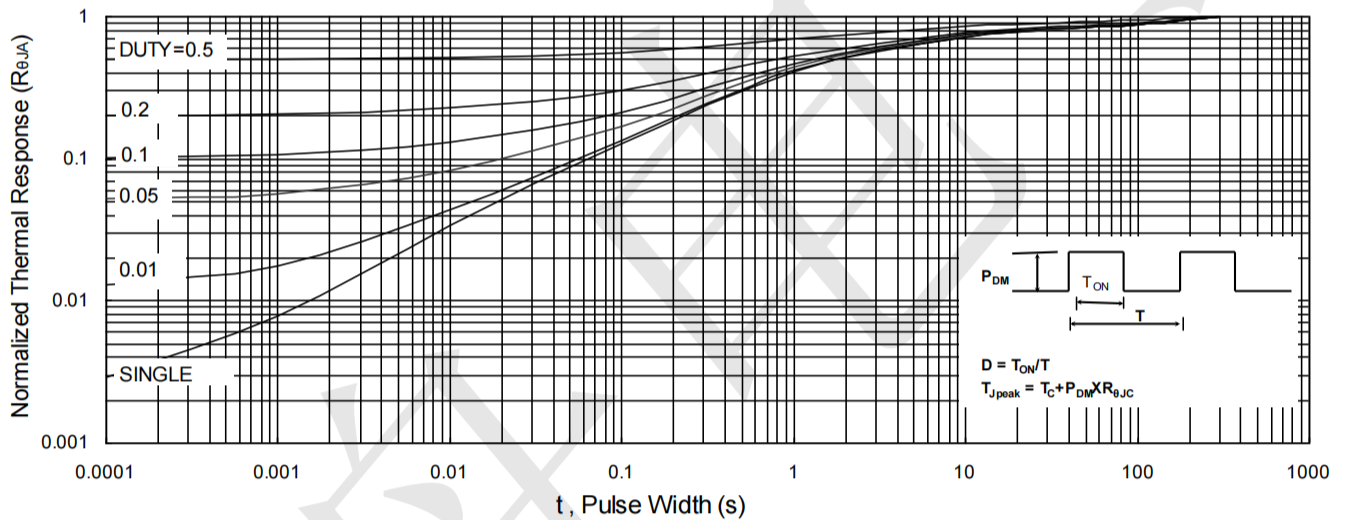


Fig.9 Normalized Maximum Transient Thermal Impedance

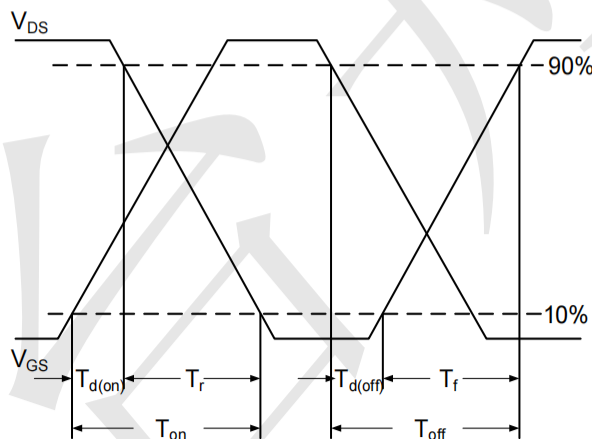


Fig.10 Switching Time Waveform

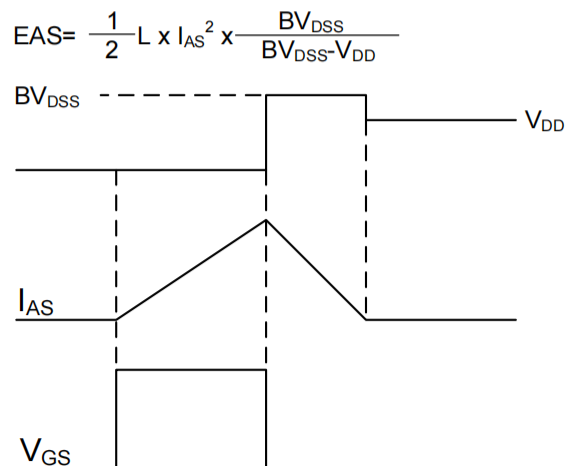
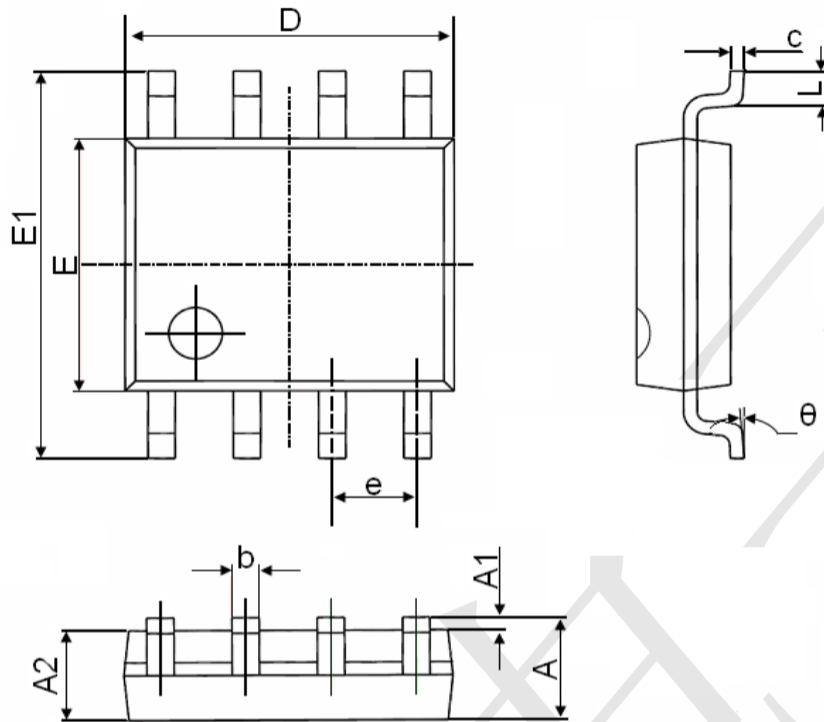


Fig.11 Unclamped Inductive Switching Waveform

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°